

## **INCHANGE SEMICONDUCTOR**

3

2.Collector

TO-3PN Package

G

R

MAX

20.30 15.50 15.70

4.90

1.10

2.10

3.60

3.20

3.40

mm

MIN

19.60

4.70

0.90

1.90

3.40

2.90

3.20

0.595 0.605

3.Emitter

PIN: 1.Base

С

# **isc Silicon PNP Power Transistors**

# MJE4350/4351/4352/4353

2 1

B

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DIM

Α

В

C

D

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J

UQ

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### DESCRIPTION

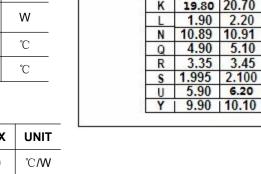
- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub> = -100V(Min)- MJE4350
    - = -120V(Min)- MJE4351
      - = -140V(Min)- MJE4352
      - = -160V(Min)- MJE4353
- Low Saturation Voltage
- Complement to the NPN MJE4340/4341/4342/4343

#### **APPLICATIONS**

· Designed for use in high power audio amplifier applications and high voltage switching regulator circuits.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)								
SYMBOL	PARAMETEI	VALUE	UNIT					
V <sub>CBO</sub>	Collector-Base Voltage	MJE4350	-100					
		MJE4351	-120	v				
		MJE4352	-140					
		MJE4353	-160	1				
V <sub>CEO</sub>	Collector-Emitter Voltage	MJE4350	-100					
		MJE4351	-120	V				
		MJE4352	-140					
		MJE4353	-160					
V <sub>EBO</sub>	Emitter-Base Voltage	-7	V					
lc	Collector Current-Continuous		-16	A				
Ісм	Collector Current-Peak		-20	A				
IB	Base Current-Continuous		-5	A				
Pc	Collector Power Dissipation @ $T_c=25^{\circ}C$		125	W				
TJ	Junction Temperature	150	°C					
T <sub>stg</sub>	Storage Temperature Ra	-65~150	°C					

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### **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case		°C/W

1

isc Website: www.iscsemi.com



## **INCHANGE SEMICONDUCTOR**

# **isc** Silicon PNP Power Transistors

# MJE4350/4351/4352/4353

### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>		MJE4350	- I <sub>C</sub> = -50mA ;I <sub>B</sub> = 0	-100		V
	Collector-Emitter Sustaining Voltage	MJE4351		-120		
		MJE4352		-140		
		MJE4353		-160		
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage		I <sub>C</sub> = -8A; I <sub>B</sub> = -0.8A		-2.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage		I <sub>C</sub> = -16A; I <sub>B</sub> = -2A		-3.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage		I <sub>C</sub> = -16A; I <sub>B</sub> = -2A		-3.9	V
$V_{\text{BE(on)}}$	Base-Emitter On Voltage		I <sub>C</sub> = -16A; V <sub>CE</sub> = -4V		-3.9	V
I <sub>CEO</sub>	Collector Cutoff Current	MJE4350	V <sub>CE</sub> = -100V; I <sub>B</sub> = 0		-0.75	- mA
		MJE4351	V <sub>CE</sub> = -120V; I <sub>B</sub> = 0		-0.75	
		MJE4352	V <sub>CE</sub> = -140V; I <sub>B</sub> = 0	-	-0.75	
		MJE4353	V <sub>CE</sub> = -160V; I <sub>B</sub> = 0	-	-0.75	
I <sub>CBO</sub>	Collector Cutoff Current		$V_{CB}$ = Rated $V_{CB}$ ; I <sub>E</sub> =0		-0.75	mA
Іево	Emitter Cutoff Current		V <sub>EB</sub> = -7V; I <sub>C</sub> =0		-1.0	mA
h <sub>FE-1</sub>	DC Current Gain		I <sub>C</sub> = -8A; V <sub>CE</sub> = -2V	15		
h <sub>FE-2</sub>	DC Current Gain		I <sub>C</sub> = -16A; V <sub>CE</sub> = -4V	8		

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